

## PATENT ABSTRACTS OF JAPAN

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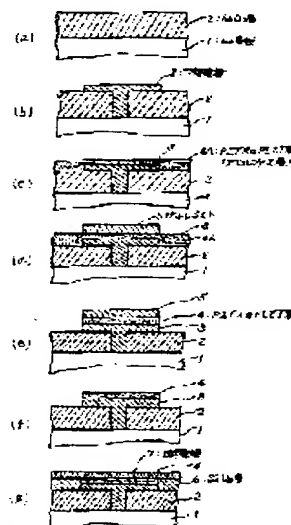
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## (54) METHOD FOR FORMING DIELECTRIC INSULATING FILM IN CHARGE STORAGE PART OF SEMICONDUCTOR

## (57)Abstract:

PURPOSE: To provide an invention characterized by patterning before crystallization annealing of PZT.

CONSTITUTION: This method executes the following: the step of forming a lower electrode 3 of a charge storage part on a substrate; the step of forming PZT or PLZT amorphous layer 4A by 120-150° C heat treatment after the lower electrode 3 is coated with a PZT or PLZT sol solution; the step of patterning of the amorphous layer 4A by photolithography etching; and the step of forming a PZT or PLZT film 4 as the dielectric insulating film by crystallization of the amorphous layer by heat treatment in an oxygen atmosphere.



## LEGAL STATUS

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